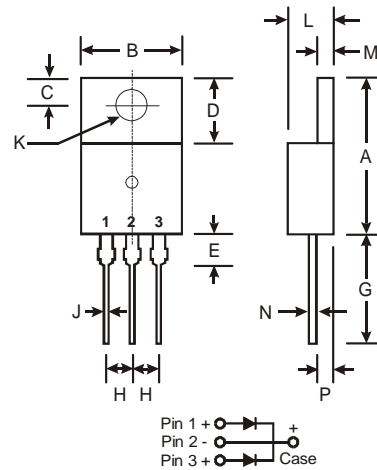


### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- **Lead Free Finish, RoHS Compliant (Note 3)**

### Mechanical Data

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Polarity: As Marked on Body
- Terminals: Finish – Tin. Solderable per MIL-STD-202, Method 208 (63)
- Marking: Type Number
- Weight: 2.24 grams (approximate)



TO-220AB		
Dim	Min	Max
A	14.48	15.75
B	10.00	10.40
C	2.54	3.43
D	5.90	6.40
E	2.80	3.93
G	12.70	14.27
H	2.40	2.70
J	0.69	0.93
K	3.54	3.78
L	4.07	4.82
M	1.15	1.39
N	0.30	0.50
P	2.04	2.79
All Dimensions in mm		

### Maximum Ratings and Electrical Characteristics @<sub>T<sub>A</sub></sub> = 25°C unless otherwise specified

Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Characteristic	Symbol	SBL 2030CT	SBL 2035CT	SBL 2040CT	SBL 2045CT	SBL 2050CT	SBL 2060CT	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>							
Working Peak Reverse Voltage	V <sub>RWM</sub>	30	35	40	45	50	60	V
DC Blocking Voltage	V <sub>R</sub>							
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1)	I <sub>O</sub>	20						A
		@ T <sub>C</sub> = 95°C						
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I <sub>FSM</sub>	250						A
Forward Voltage Drop	V <sub>FM</sub>	0.55				0.75		V
		@ I <sub>F</sub> = 10A, T <sub>C</sub> = 25°C						
Peak Reverse Current	I <sub>RM</sub>					1.0		mA
		@ T <sub>C</sub> = 25°C						
at Rated DC Blocking Voltage	I <sub>RM</sub>					50		
		@ T <sub>C</sub> = 100°C						
Typical Junction Capacitance (Note 2)	C <sub>j</sub>	650						pF
Typical Thermal Resistance Junction to Case (Note 1)	R <sub>θJC</sub>	2.8						°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150						°C

- Notes:
1. Thermal resistance junction to case mounted on heatsink.
  2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
  3. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied, see EU Directive 2002/95/EC Annex Notes.

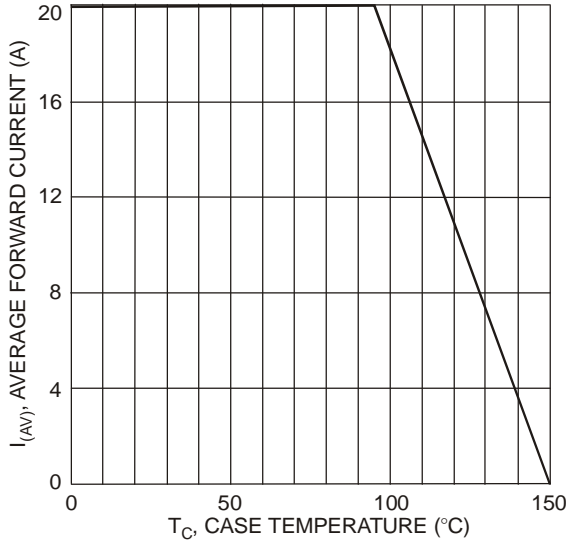


Fig. 1 Forward Current Derating Curve

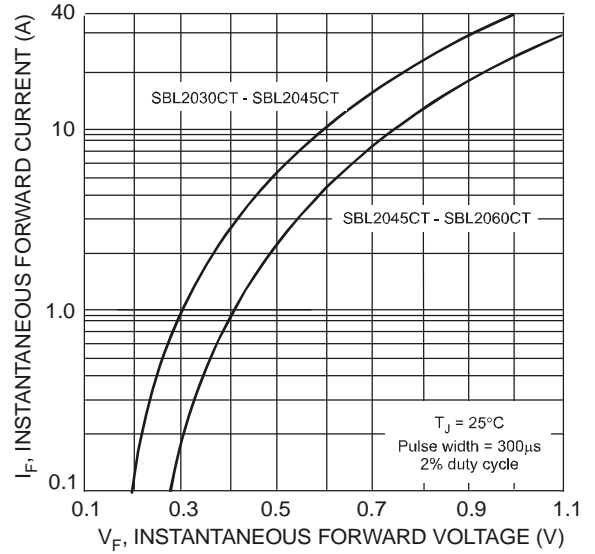


Fig. 2 Typical Forward Voltage

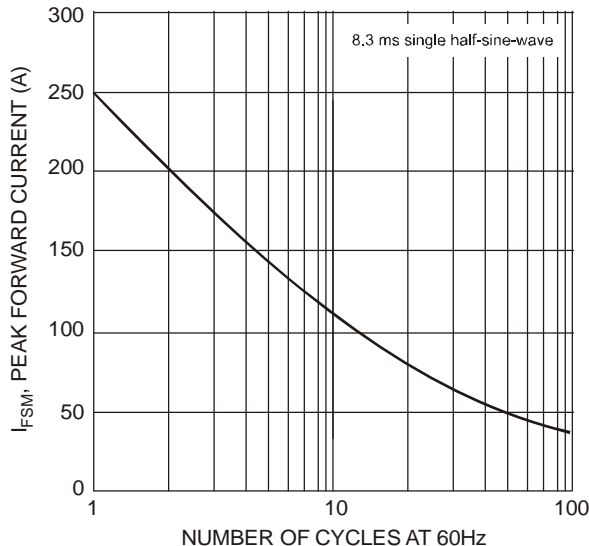


Fig. 3 Maximum Non-Repetitive Surge Current

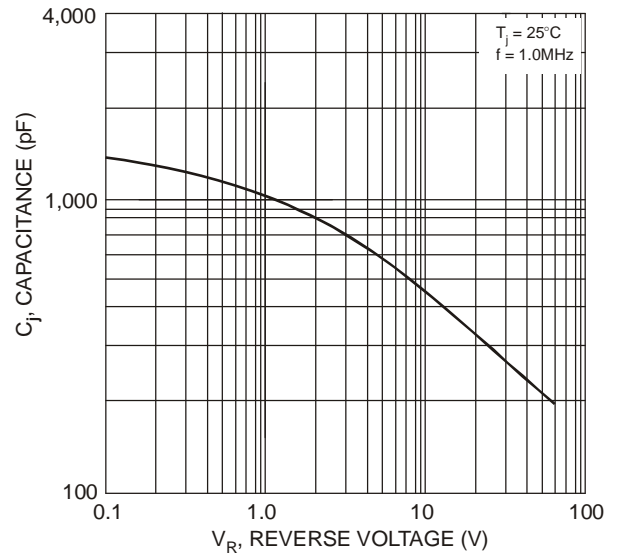


Fig. 4 Typical Junction Capacitance

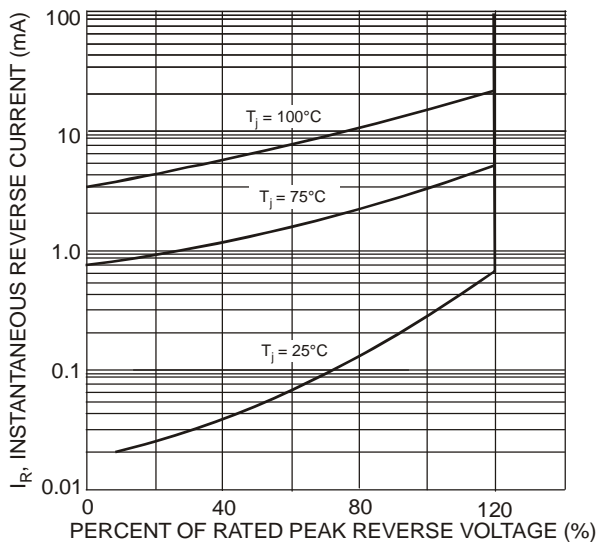


Fig. 5 Typical Reverse Characteristics



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**Ordering Information** (Note 4)

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Device	Packaging	Shipping
SBL20xxCT*	TO-220AB	50/Tube

\* xx = Device type, e.g. SBL2045CT

Notes: 4. For packaging details, visit our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

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